



TPS40197 4 ビット VID インターフェイス搭載、 4.5V~14V 入力、6A 降圧型コントローラ

1 特長

- 入力電圧範囲：4.5V~14V
- 4 ビットのダイナミック VID オンザフライをサポート
- VID の出力電圧と遷移レートをプログラム可能
- 520kHz の固定スイッチング周波数
- 選択可能なローサイド (3 種類の設定) と固定のハイサイドによる温度補償付き過電流保護
- パワー・グッド・インジケータ
- 5V レギュレータ内蔵
- 電圧モード制御
- 内部で固定された 5.5ms ソフトスタート時間
- プリバイアス出力対応
- 140°Cのサーマル・シャットダウン
- 16 ピン QFN パッケージ

2 アプリケーション

- Smart-Reflex™ DSP
- POL モジュール
- 通信機器

3 概要

TPS40197 は、4.5V~14V の公称入力電源電圧で動作する同期整流降圧型コントローラです。このコントローラは、スイッチング周波数を 520kHz に固定した電圧モード制御アーキテクチャを実装しています。スイッチング周波数が高いため、小型のインダクタおよび出力コンデンサを使用でき、コンパクトな電源ソリューションを構築できます。適応型のクロス導通防止方式により、パワーFETを流れる貫通電流が防止されます。

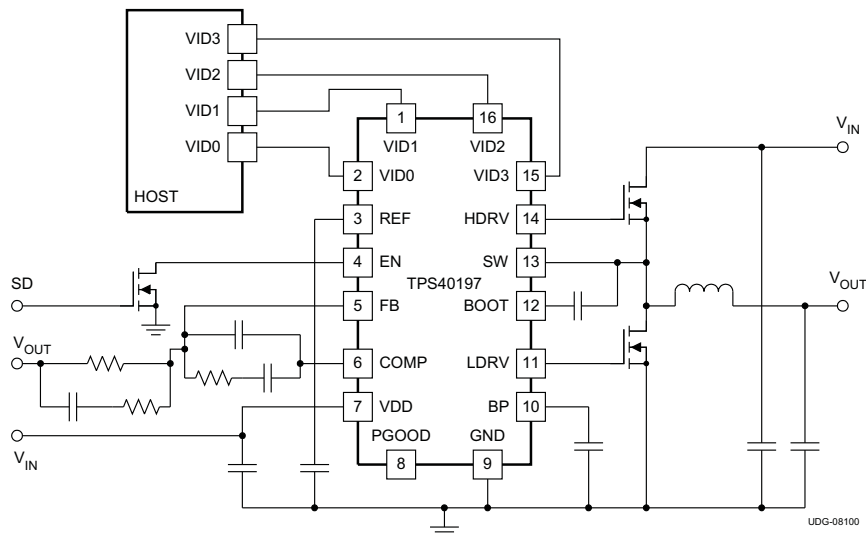
TPS40197 は、プログラム可能な遷移レートで VID をシームレスかつ即時に変更できるように、PWM 制御と 4 ビット VID インターフェイスを 1 つのチップに統合しています。本デバイスは、Smart-Reflex™ DSP コア用のシンプルな電源ソリューションとして使用できます。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
TPS40197	VQFN (16)	4.50mm × 3.50mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

代表的なアプリケーション回路



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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision A (July 2012) から Revision B に変更 Page

- 編集上の変更のみ、技術上の変更なし..... 1

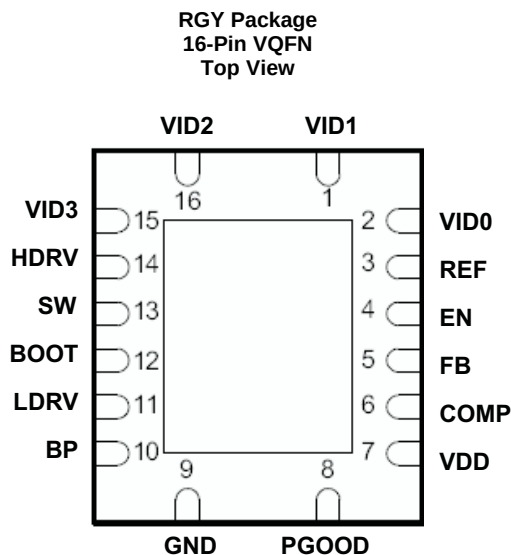
2008年11月発行のものから更新 Page

- Added a new paragraph to the Enable section 13

5 概要(続き)

短絡検出は、ローサイド FET がオンのとき、その両端の電圧降下を検出し、ユーザーが選択したスレッショルド (100mV、200mV、280mV のいずれか) と比較することで行います。このスレッショルドは、COMPからGNDに接続されている、単一の外付け抵抗により設定されます。この抵抗はスタートアップ時に検出され、選択されたスレッショルドがラッチされます。パルス単位の制限 (電流暴走防止用) は、ハイサイド FET がオンのとき、その両端の電圧を検出し、その電圧降下が固定スレッショルド (550mV) を超過したときにサイクルを中断することで行います。コントローラが出力の短絡を検出した場合、両方の FET はオフになり、タイムアウト期間が終了するまで再起動を試みません。これにより、持続的フォルトが発生した場合の消費電力を制限します。

6 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
BOOT	12	I	Gate drive voltage for the high-side N-channel MOSFET. A 100-nF capacitor (typical) must be connected between this pin and SW.
BP	10	O	Output bypass for the internal regulator. Connect a low ESR bypass ceramic capacitor of 1 μ F or greater from this pin to GND.
COMP	6	O	Output of the error amplifier and connection node for loop feedback components.
EN	4	I	Logic level input which starts or stops the controller from an external user command. A high level turns the controller on. A weak internal pullup holds this pin high so that the pin may be left floating if this function is not used. Pulling this pin low disables the controller.
FB	5	I	Inverting input to the error amplifier.
HDRV	14	O	Bootstrapped gate drive output for the high-side N-channel MOSFET.
LDRV	11	O	Gate drive output for the low-side synchronous rectifier N-channel MOSFET.
PGOOD	8	O	Open drain power good output.
REF	3	I	Non-Inverting input to the error amplifier. Its voltage range is from 0.9 V to 1.2 V in 20-mV steps. It is also internally connected to the DAC output through a unit gain buffer with 650- μ A source/sink current capability. An external capacitor connected from this pin to GND programs the output voltage transition rate when VID code changes.
VDD	7	I	Power input to the controller. Connect a 1- μ F bypass capacitor closely from this pin to GND.
VID0	2	I	Logic level inputs to the internal DAC that provides the reference voltage for output regulation. These pins are internally pulled up to a 1.68-V source with 80- μ A pullup current.
VID1	1	I	
VID2	16	I	
VID3	15	I	
GND	9		Ground connection to the controller

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		VALUE	UNIT
Input voltage	VDD, EN	–0.3 to 20	V
	SW	–5 to 25	
	BOOT, HDRV	–0.3 to 30	
	BOOT–SW, HDRV–SW	–0.3 to 6	
	FB, BP, LDRV, PGOOD, REF	–0.3 to 6	
Output voltage	COMP	–0.3 to 3.5	V
	VID0, VID1, VID2, VID3	–0.3 to 2	
Operating junction temperature range, T _J		–40 to 150	°C
Storage temperature, T _{stg}		–55 to 150	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	2500	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Supply voltage	VDD	4.5	14	V
Operating junction temperature, T _J		–40	125	°C

7.4 Package Dissipation Ratings

PACKAGE	AIRFLOW (LFM)	R _{θJA} HIGH-K Board ⁽¹⁾ (°C/W)	POWER RATING (W) T _A = 25°C	POWER RATING (W) T _A = 85°C
16-Pin Plastic Quad Flatpack (RGY)	0 (Natural Convection)	49.2	2.0	0.81
	200	41.2	2.4	0.97
	400	37.7	2.6	1.00

- (1) Ratings based on JEDEC High Thermal Conductivity (High K) Board. For more information on the test method, see TI Technical Brief SZZA017.

7.5 Electrical Characteristics

–40°C ≤ T_J ≤ 85°C, V_{VDD} = 12 V, all parameters at zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOLTAGE REFERENCE AND VID						
V _{FB}	FB input voltage	0.9 V ≤ V _{VID} ≤ 1.2 V, 0°C ≤ T _J ≤ 85°C	−0.5%		0.5%	V _{VID}
		0.9 V ≤ V _{VID} ≤ 1.2 V, −40°C ≤ T _J ≤ 85°C	−1.0%		1.0%	
I _{VID}	VID pullup current		50	80	120	μA
V _{VID}	VID pullup voltage		1.60	1.68	1.78	V
t _{ANTI-SKEW (1)}	Anti-skew filtering time		300	550	750	ns
V _{VIDH}	VID high-level input voltage		0.8	1.0	1.3	V
V _{VIDL}	VID low-level input voltage		0.30	0.55	0.70	V
I _{REF}	REF source/sink current		400	650	850	μA
INPUT SUPPLY						
V _{VDD}	Normal input supply voltage range		4.5		14.0	V
I _{VDD}	Operating current	V _{ENABLE} = 3 V		2.5	4.5	mA
		V _{ENABLE} = 0.6 V		45	70	μA
SOFT START						
t _{SS}	Soft-start time		3.3	5.5	7	ms
t _{SSDLY}	Soft-start delay time		1.3	2.3	4	
t _{REG}	Time to regulation		5.0	8.0	11	
ON-BOARD REGULATOR						
V _{BP}	Output voltage	V _{VDD} > 6 V, I _{BP} ≤ 10 mA	5.1	5.3	5.5	V
V _{DO}	Regulator dropout voltage (V _{VDD} −V _{BP})	V _{VDD} > 5 V, I _{BP} ≤ 25 mA		350	550	mV
I _{SC}	Regulator current limit threshold		50			mA
I _{BP}	Average current				50	
OSCILLATOR						
f _{SW}	Switching frequency		420	520	600	kHz
V _{RAMP} ⁽¹⁾	Ramp amplitude			1		V
PWM						
D _{MAX} ⁽¹⁾	Maximum duty cycle		85%			ns
t _{ON(min)} ⁽¹⁾	Minimum controllable pulse				110	
t _{DEAD}	Output driver dead time	HDRV off to LDRV on		50		
		LDRV off to HDRV on		25		
ERROR AMPLIFIER						
G _{BWP} ⁽¹⁾	Gain bandwidth product		7	10		MHz
A _{OL} ⁽¹⁾	Open loop gain		60			dB
I _{IB}	Input bias current (current out of FB pin)				100	nA
I _{EAOP}	Output source current	V _{FB} = 0 V	1			mA
I _{EAOM}	Output sink current	V _{FB} = 2 V	1			
UNDERVOLTAGE LOCKOUT						
V _{UVLO}	Turn-on voltage		3.9	4.2	4.4	V
UVLO _{HYST}	Hysteresis		700	850	1000	mV
SHUTDOWN						
V _{IH}	High-level input voltage, ENABLE			1.9	3	V
V _{IL}	Low-level input voltage, ENABLE		0.6	1.2		

(1) Specified by design. Not production tested.

Electrical Characteristics (continued)

–40°C ≤ T_J ≤ 85°C, V_{VDD} = 12 V, all parameters at zero power dissipation (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OUTPUT DRIVERS						
R _{HDHI}	High-side driver pull-up resistance	(V _{BOOT} – V _{SW}) - 4.5 V, I _{HDR} V = – 100 mA		3	6	Ω
R _{HDLO}	High-side driver pull-down resistance	(V _{BOOT} – V _{SW}) - 4.5 V, I _{HDR} V = 100 mA		1.5	3	
R _{LDHI}	Low-side driver pull-up resistance	I _{LDRV} = –100 mA		2.5	5	
R _{LDLO}	Low-side driver pull-down resistance	I _{LDRV} = 100 mA		0.8	1.5	
t _{HRISE} ⁽¹⁾	High-side driver rise time	C _{LOAD} = 1 nF		15	35	ns
t _{HFALL} ⁽¹⁾	High-side driver fall time			10	25	
t _{LRISE} ⁽¹⁾	Low-side driver rise time			15	35	
t _{LFALL} ⁽¹⁾	Low-side driver fall time			10	25	
SHORT CIRCUIT PROTECTION						
t _{PSS(min)} ⁽¹⁾	Minimum pulse time during short circuit			250		ns
t _{BLNK} ⁽¹⁾	Switch leading-edge blanking pulse time		60	90	120	
t _{OFF}	Off-time between restart attempts		30	50		ms
V _{ILIM}	Short circuit comparator threshold voltage	R _{COMP(GND)} = OPEN, T _J = 25°C	160	200	240	mV
		R _{COMP(GND)} = 4 kΩ, T _J = 25°C	80	100	120	
		R _{COMP(GND)} = 12 kΩ, T _J = 25°C	228	280	342	
V _{ILIMH}	Short circuit threshold voltage on high-side MOSFET	T _J = 25°C	400	550	650	
POWER GOOD						
V _{OV}	Feedback voltage limit for powergood		106%	110%	114%	VID
V _{UV}			86%	90%	94%	
V _{PG_HYST}	Powergood hysteresis voltage at FB pin		10	30	70	mV
R _{PGD}	Pull-down resistance of PGD pin	V _{FB} < 90% V _{VID} mV or V _{FB} > 110% V _{VID}		7	50	Ω
I _{PDGLK}	Leakage current	90% V _{VID} ≤ V _{FB} ≤ 100% V _{VID} , V _{PGOOD} = 5 V		7	12	μA
BOOT DIODE						
V _{DFWD}		I _{BOOT} = 5 mA	0.5	0.8	1.2	V
THERMAL SHUTDOWN						
T _{JSD} ⁽¹⁾	Junction shutdown temperature			140		°C
T _{JSDH} ⁽¹⁾	Hysteresis			20		

7.6 Typical Characteristics

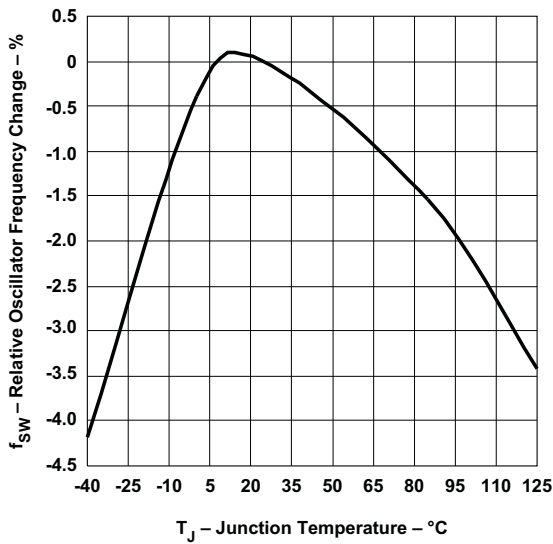


Figure 1. Relative Oscillator Frequency vs Junction Temperature

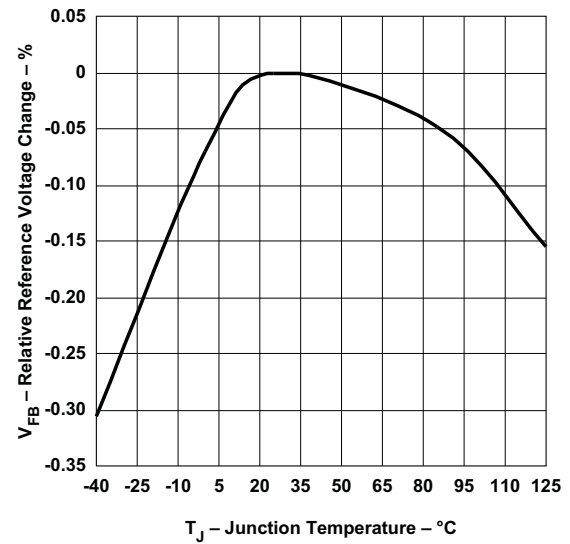


Figure 2. Relative Reference Voltage Change vs Junction Temperature

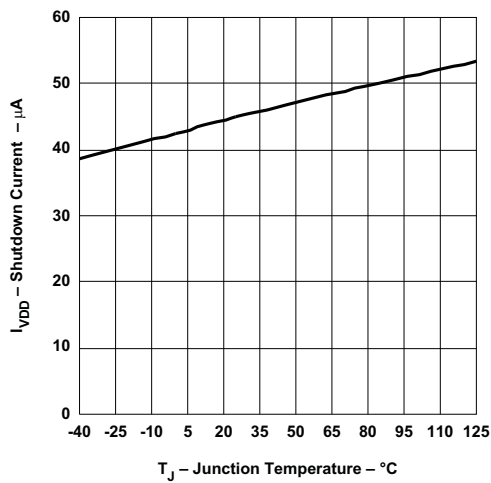


Figure 3. Shutdown Current vs Junction Temperature

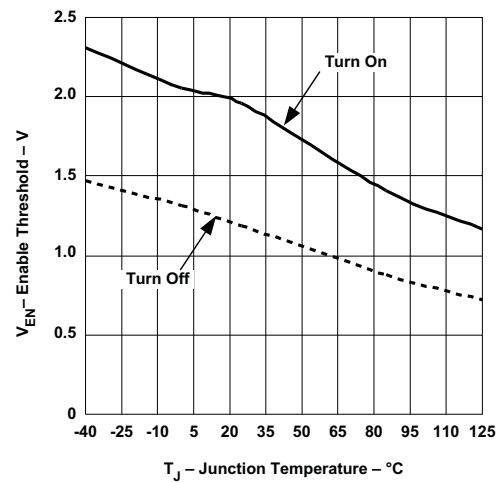


Figure 4. Enable Threshold vs Junction Temperature

Typical Characteristics (continued)

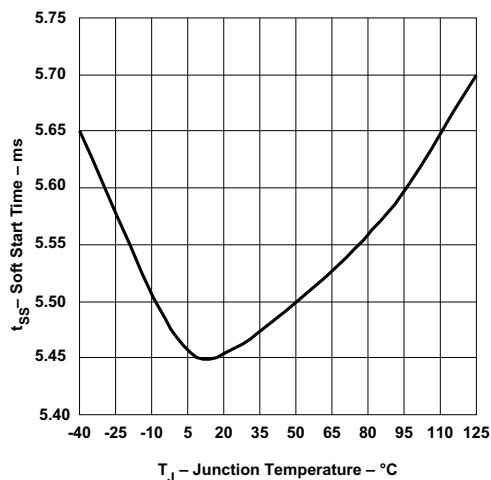


Figure 5. Soft-Start Time vs Junction Temperature

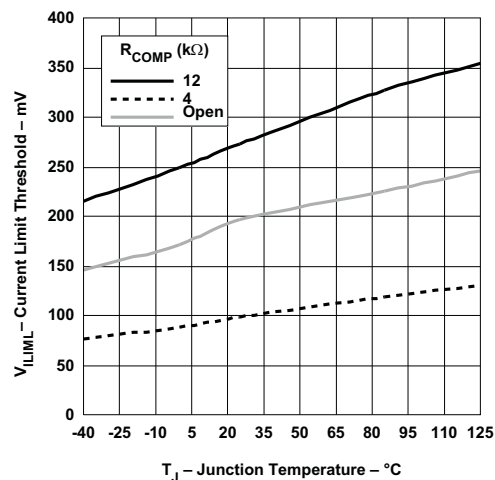


Figure 6. Low-Side MOSFET Current Limit Threshold vs Junction Temperature

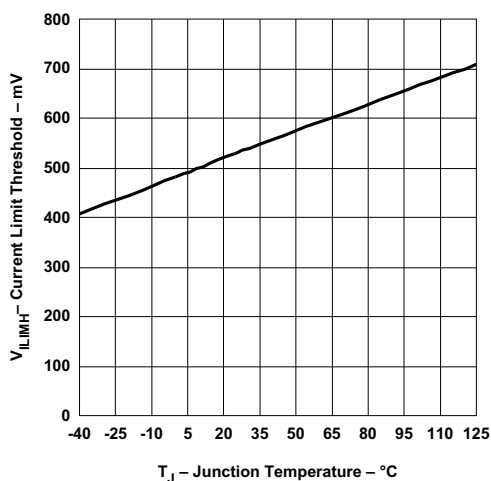


Figure 7. High-Side MOSFET Current Limit Threshold vs Junction Temperature

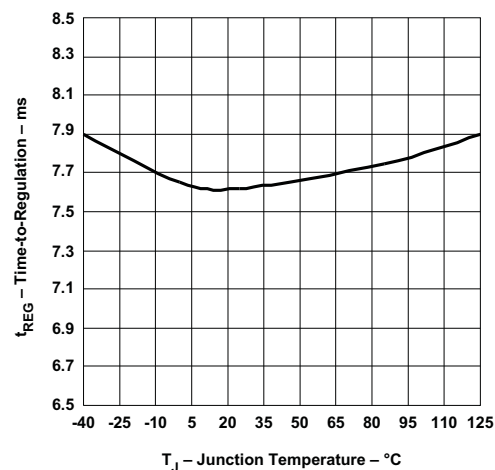


Figure 8. Total Time-To-Regulation vs Junction Temperature

Typical Characteristics (continued)

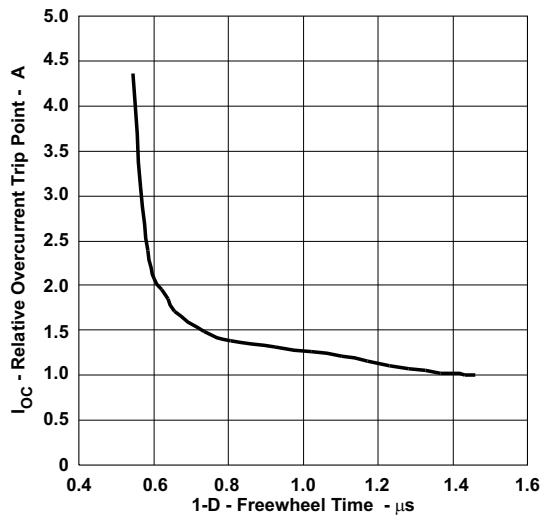


Figure 9. Relative Overcurrent Trip Point vs Freewheel Time

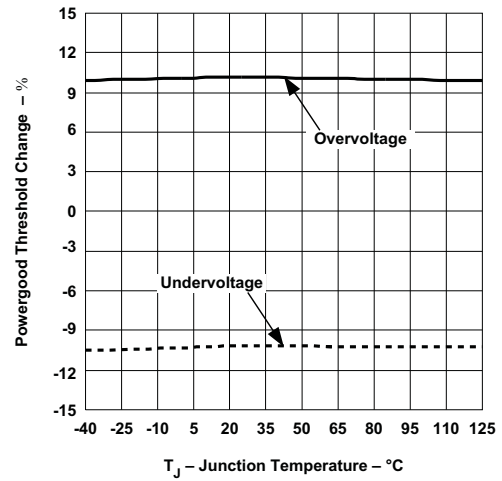


Figure 10. Relative Power Good Threshold vs Junction Temperature

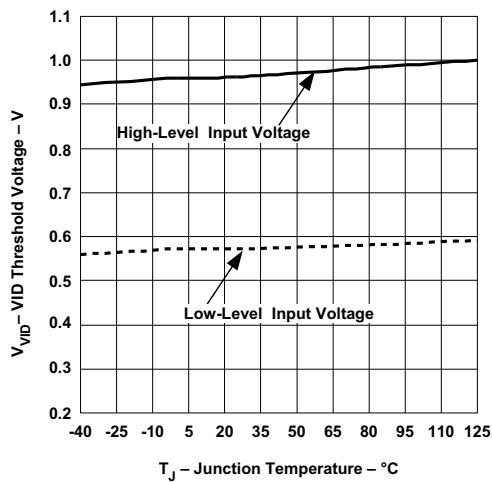


Figure 11. VID Threshold Voltage vs Junction Temperature

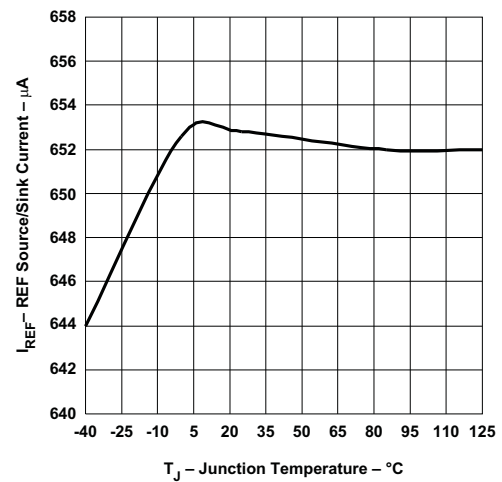


Figure 12. REF Source/Sink Current vs Junction Temperature

Typical Characteristics (continued)

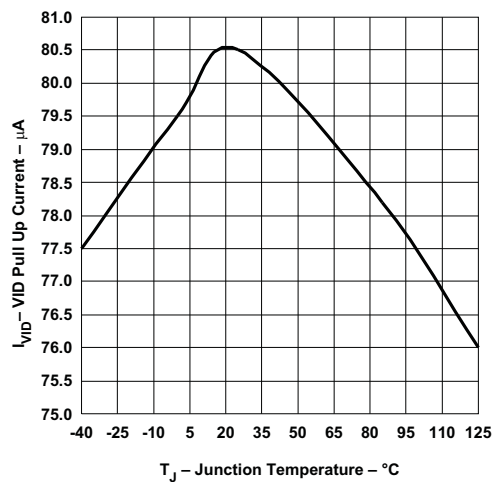


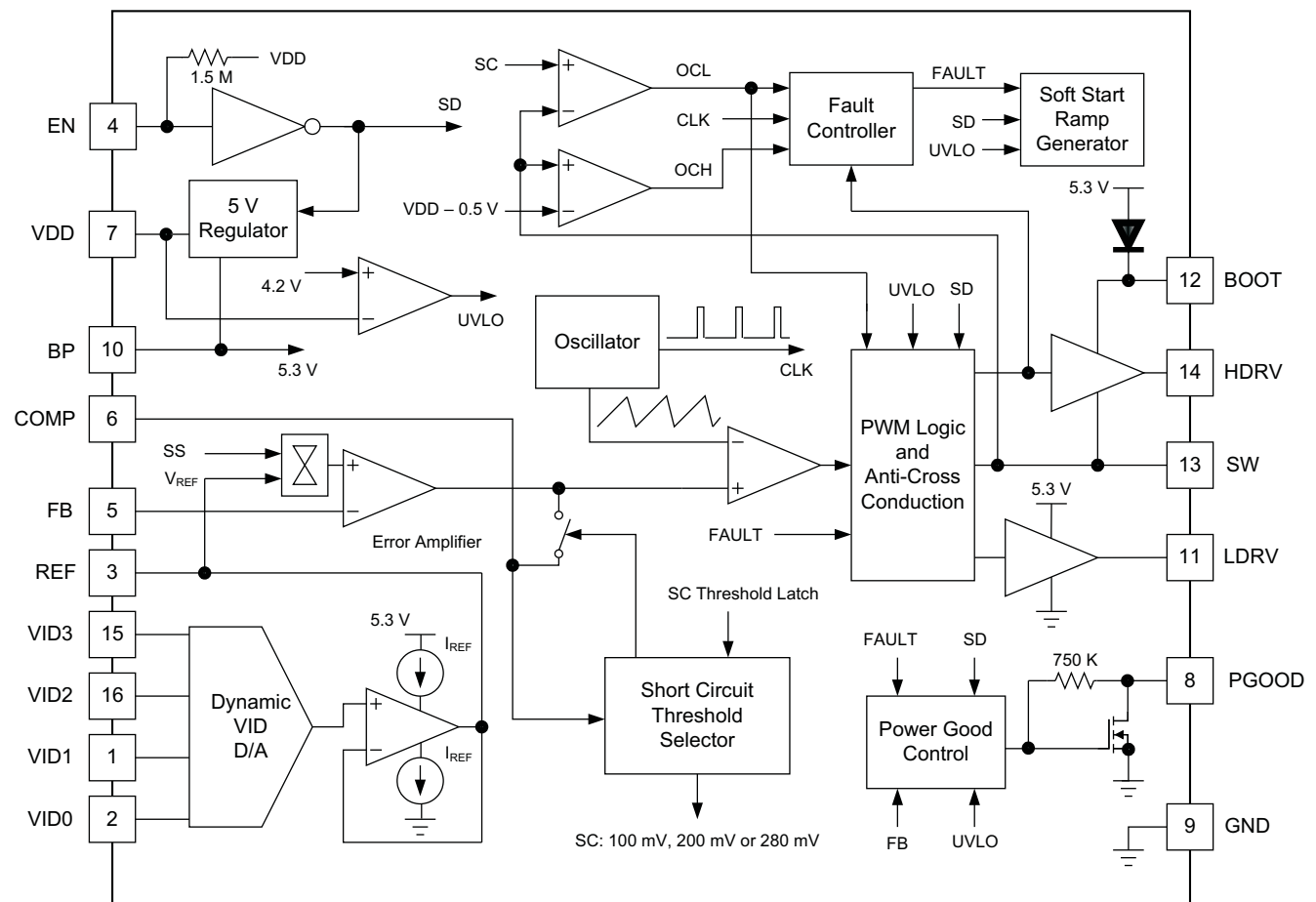
Figure 13. VID Pullup Current vs Junction Temperature

8 Detailed Description

8.1 Overview

The TPS40197 is a synchronous buck controller which provides all the necessary features to construct a high-performance DC/DC converter. Support for pre-biased outputs eliminates concerns about damaging sensitive loads during startup. Strong gate drivers for the high-side and rectifier MOSFETs decrease switching losses for increased efficiency. Adaptive gate drive timing prevents shoot through and minimizes body diode conduction in the rectifier MOSFET, also increasing efficiency. Selectable short-circuit protection thresholds and hiccup recovery from a short-circuit increase design flexibility and minimize power dissipation in the event of a prolonged output fault. A dedicated enable pin allows the converter to be placed in a very low quiescent current shutdown mode. Internally fixed switching frequency and soft-start time reduce external component count, simplifying design and layout, as well as reducing footprint and cost. The dynamic voltage identification (VID) circuitry is designed to provide Smart-Reflex™ power supply solution to DSPs with core voltage optimization.

8.2 Functional Block Diagram



Feature Description (continued)

8.3.4 Start-up Sequence and Timing

The TPS40197 startup sequence is as follows. After input power is applied, the 5-V onboard regulator initiates. Once this regulator comes up, the device goes through a period where it samples the impedance at the COMP pin and determines the short-circuit protection threshold voltage, by placing 400 mV on the COMP pin for approximately 1.15 ms. During this time, the current is measured and compared against internal thresholds to select the short circuit protection threshold. After this, the COMP pin is brought low for 1.15 ms. This ensures that the feedback loop is preconditioned at startup and no sudden output rise occurs at the output of the converter when the converter is allowed to start switching. After these initial 2.3 ms, the internal soft-start circuitry is engaged and the converter is allowed to start as shown in [Figure 15](#).

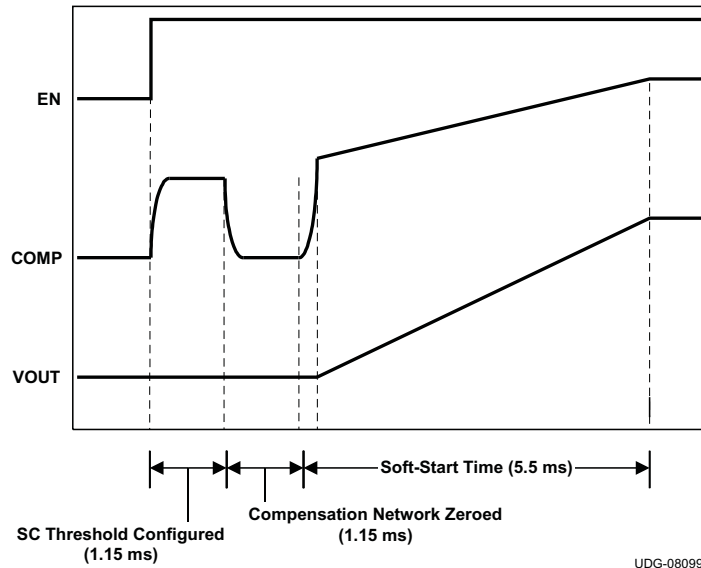


Figure 15. Start-up Sequence

8.3.5 Selecting the Short Circuit Current

A short circuit in the TPS40197 is detected by sensing the voltage drop across the low-side FET when it is on, and across the high-side FET when it is on. If the voltage drop across either FET exceeds the short-circuit threshold in any given switching cycle, a counter increments one count. If the voltage across the high-side FET was higher than the short circuit threshold, that FET is turned off early. If the voltage drop across either FET does not exceed the short circuit threshold during a cycle, the counter is decremented for that cycle. If the counter fills up (a count of 7) a fault condition is declared and the drivers turn off both MOSFETs. After a timeout of approximately 50 ms, the controller attempts to restart. If a short circuit continues at the output, the current quickly ramps up to the short-circuit threshold and another fault condition is declared and the process of waiting for the 50 ms and attempting to restart repeats. The low-side threshold increases as the low-side on time decreases due to blanking time and comparator response time. See [Figure 9](#) for changes in the threshold as the low-side FET conduction time decreases.

The TPS40197 provides three selectable short-circuit protection thresholds for the low-side FET: 100 mV, 200 mV, and 280 mV. The particular threshold is selected by connecting a resistor from COMP to GND. [Table 1](#) shows the short-circuit thresholds for corresponding resistors from COMP to GND. When designing the compensation for the feedback loop, remember that a low impedance compensation network combined with a long network time constant can cause the short-circuit threshold setting to not be as expected. The time constant and impedance of the network connected from COMP to FB must be as in [Equation 1](#) to ensure no interaction with the short-circuit threshold setting.

Feature Description (continued)

$$\left(\frac{0.4 \text{ V}}{R1} \right) \times e^{\left(\frac{-t}{R1 \times C1} \right)} \leq 10 \mu\text{A}$$

where

- t is 1.15 ms, the sampling time of the short circuit threshold setting circuit
- R1 and C1 are the values of the components in [Figure 16](#)

(1)

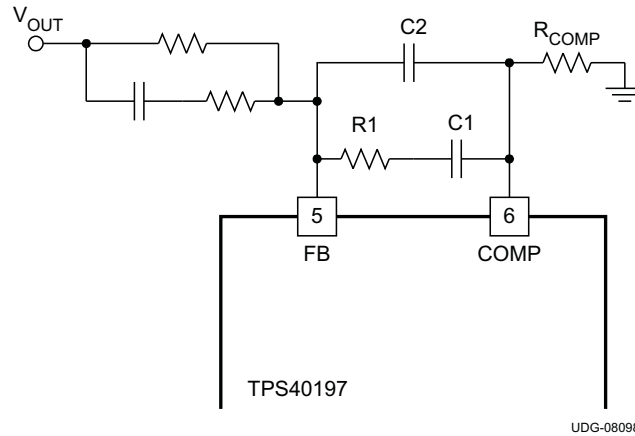


Figure 16. Short Circuit Threshold Feedback Network

Table 1. Circuit Threshold Voltage Selection

COMPARATOR RESISTANCE R _{COMP} (kΩ)	CURRENT LIMIT THRESHOLD VOLTAGE V _{ILIM} (mV)
12 ±10%	280
OPEN	200
4 ±10%	100

The range of expected short-circuit current thresholds is shown in [Equation 2](#) and [Equation 3](#).

$$I_{SCP(max)} = \frac{V_{ILIM(max)}}{R_{DS(on)min}}$$

(2)

$$I_{SCP(min)} = \frac{V_{ILIM(min)}}{R_{DS(on)max}}$$

where

- I_{SCP} is the short circuit current
- V_{ILIM} is the short-circuit threshold for the low-side MOSFET
- R_{DS(on)} is the channel resistance of the low-side MOSFET

(3)

Note that due to blanking time considerations, overcurrent threshold accuracy may fall off for duty cycle greater than 75% because the overcurrent comparator has only a very short time to sample the SW pin voltage under these conditions and may not have time to respond to voltages very near the threshold.

The short-circuit protection threshold for the high-side MOSFET is fixed at 550 mV typical, 400 mV minimum. This threshold is in place to provide a maximum current output using pulse-by-pulse current limit in the case of a fault. The pulse terminates when the voltage drop across the high-side FET exceeds the short-circuit threshold. The maximum amount of current that can be specified to be sourced from a converter can be found by [Equation 4](#).

$$I_{OUT(max)} = \frac{V_{ILIMH(min)}}{R_{DS(on)max}}$$

where

- $I_{OUT(max)}$ is the maximum current that the converter is specified to source
- $V_{ILIMH(min)}$ is the short-circuit threshold for the high-side MOSFET (400 mV)
- $R_{DS(on)max}$ is the maximum resistance of the high-side MOSFET

(4)

If the required current from the converter is greater than the calculated $I_{OUT(max)}$, a lower resistance high-side MOSFET must be chosen. Both the high-side and low-side thresholds use temperature compensation to approximate the change in resistance for a typical power MOSFET. This helps counteract shifts in overcurrent thresholds as temperature increases. For this to be effective, the MOSFETs and the device must be well coupled thermally.

8.3.6 Voltage Reference and Dynamic VID

To provide optimized voltage for Smart-Reflex™ DSP cores, the TPS40197 is designed to monitor the VID code at all times once soft-start is complete, and actively adjusts its output voltage if the VID code should change during normal operation. A digital-to-analog converter (DAC) generates a reference voltage based on the state of logical signals at pins VID0 through VID3. The DAC decodes the 4-bit logic signal into one of the discrete voltages shown in [Table 2](#). The default setting for the output is 1.2 V (VID code 1111). The output voltage is 1.2 V during initial start or restart after cycling the input, toggling EN pin or recovering from a short circuit at the output.

To ensure that no erroneous output voltage is produced, the TPS40197 VID inputs have internal anti-skew circuit with approximately 550 ns of filtering time. Each VID input is pulled up to an internal 1.68-V source with 80-μA pullup current for use with open-drain outputs.

The output voltage can be programmed from 0.9 V to 1.2 V in 20 mV steps. Smooth upward and downward core voltage transition can be achieved by programming the transition rate with an external capacitor connected from REF pin to GND. The required capacitance can be calculated using [Equation 5](#).

$$C_{REF} = \frac{(I_{REF} \times T_{TR})}{V_{VID-TR}}$$

where

- V_{VID-TR} is the total voltage transition through VID
- I_{REF} is the internal reference source/sink current
- T_{TR} is the intended total VID voltage transition time

(5)

C_{REF} must be limited to a maximum of 1.5 μF to avoid interfering with the soft start. A capacitor (C_{REF}) with a minimum capacitance of 100-nF is also recommended.

Table 2. Voltage Identification Codes

VID TERMINALS (0 = LOW, 1 = HIGH)				V _{REF}
VID3	VID2	VID1	VID0	(V _{dc})
0	0	0	0	0.90
0	0	0	1	0.92
0	0	1	0	0.94
0	0	1	1	0.96
0	1	0	0	0.98
0	1	0	1	1.00
0	1	1	0	1.02
0	1	1	1	1.04
1	0	0	0	1.06
1	0	0	1	1.08
1	0	1	0	1.10
1	0	1	1	1.12
1	1	0	0	1.14
1	1	0	1	1.16
1	1	1	0	1.18
1	1	1	1	1.20

8.3.7 Minimum On-Time Consideration

The TPS40197 has a minimum on-time of 110 ns (maximum). With the restriction of this minimum on-time, the device may begin to skip pulses to effectively lower the overall on-time to keep the output in regulation when operating at high input-to-output conversion ratio. If pulse skipping is undesirable for some reason, it is recommended that the maximum input voltage be limited to 13.5 V.

8.3.8 BP Regulator

The TPS40197 has an on board 5-V BP regulator that allows the parts to operate from a single voltage feed. No separate 5-V feed to the part is required. This regulator needs to have a minimum of 1-μF of capacitance on the BP pin for stability. A ceramic capacitor is suggested for this purpose.

This regulator can also be used to supply power to nearby circuitry, eliminating the need for a separate LDO in some cases. If this pin is used for external loads, be aware that this is the power supply for the internals of the TPS40197. While efforts have been made to reduce sensitivity, any noise induced on this line has an adverse effect on the overall performance of the internal circuitry and shows up as increased pulse jitter, or skewed reference voltage. Also, when the device is disabled by pulling the EN pin low, this regulator is turned off and will not be available to supply power.

The amount of power available from this pin varies with the size of the power MOSFETs that the drivers must operate. Larger MOSFETs require more gate drive current and reduce the amount of power available on this pin for other tasks. The total current that can be drawn from this pin by both the gate drive and external loads cannot exceed 50 mA. The device itself consumes up to 4 mA from the regulator and the total gate drive current can be found from [Equation 6](#).

8.3.9 Prebias Start-up

The TPS40197 contains a unique circuit to prevent current from being pulled from the output during startup in the condition the output is prebiased. When the soft start commands a voltage higher than the pre-bias level (internal soft-start becomes greater than feedback voltage [V_{FB}]), the controller slowly activates synchronous rectification by starting the first LDRV pulse with a narrow on-time. It then increments that on-time on a cycle-by-cycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-bias output, and ensures that the output voltage (V_{OUT}) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation with minimal disturbance to the output voltage. The amount of time from the start of switching until the low-side MOSFET is turned on for the full (1-D) interval is defined by 32 clock cycles.

8.3.10 Drivers

The drivers for the external HDRV and LDRV MOSFETs are capable of driving a gate-to-source voltage of 5 V. The LDRV driver switches between BP and GND, while HDRV driver is referenced to SW and switches between BOOT and SW. The drivers have non-overlapping timing that is governed by an adaptive delay circuit to minimize body diode conduction in the synchronous rectifier. The drivers are capable of driving MOSFETS that are appropriate for a 15-A converter.

8.3.11 Power Good

The TPS40197 provides an indication that output power is good for the converter. This is an open drain signal and pulls low when any condition exists that would indicate that the output of the supply might be out of regulation. These conditions include:

- V_{FB} is more than 10% from the reference voltage based on VID codes
- soft-start is active
- an undervoltage condition exists for the device
- a short-circuit condition has been detected
- die temperature is over (140°C)

NOTE

When there is no power to the device, PGOOD is not able to pull close to GND if an auxiliary supply is used for the power good indication. In this case, a built in resistor connected from drain to gate on the PGOOD pull down device makes the PGOOD pin look approximately like a diode to GND.

8.3.12 Thermal Shutdown

If the junction temperature of the device reaches the thermal shutdown limit of 140°C, the PWM and the oscillator are turned off and HDRV and LDRV are driven low, turning off both FETs. When the junction cools to the required level (120°C nominal), the PWM initiates soft-start as during a normal power-up cycle.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPS40197 is a synchronous buck controller that operates from 4.5-V to 14-V input supply nominally. The controller implements voltage-mode control architecture with the switching frequency fixed at 520 kHz. The higher switching frequency facilitates the use of smaller inductor and output capacitors, thereby providing a compact power-supply solution.

9.2 Typical Application

The schematic for the design is shown in [Figure 17](#) and the list of materials is shown in [Table 3](#).

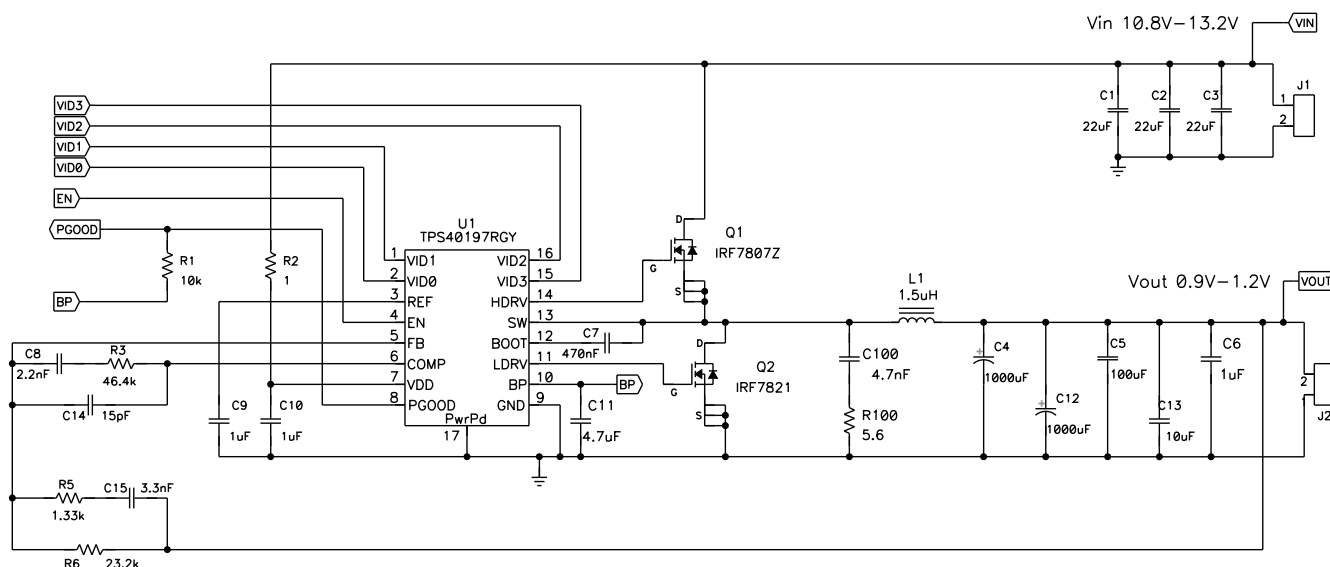


Figure 17. TPS40197 Sample Schematic

Typical Application (continued)

9.2.1 Design Requirements

Table 3. Design Example List Of Materials

REFERENCE DESIGNATOR	QTY	DESCRIPTION	MFR	PART NUMBER
C1, C2, C3	3	Capacitor, ceramic, 16 V, X7R, 20%, 22 μ F, 1210	TDK	C3225X7R1C226K
C4, C12	2	Capacitor, POSCAP, 2.5 V, 20%, 1 mF, 5 m Ω , D4D	Sanyo	2R5TPD1000M5
C5	1	Capacitor, ceramic, 6.3 V, X5R, 20%, 100 μ F, 1210	TDK	C3225X5R0J107K
C6, C9, C10	3	Capacitor, ceramic, 16 V, X7R, 20%, 1 μ F, 0603	Std	Std
C7	1	Capacitor, ceramic, 10 V, X5R, 20%, 470 nF, 0603	Std	Std
C8	1	Capacitor, ceramic, 50 V, NPO, 10%, 2.2 nF, 0603	Std	Std
C11	1	Capacitor, ceramic, 6.3 V, X5R, 20%, 4.7 μ F, 0603	TDK	C1608X5R0J475K
C13	1	Capacitor, ceramic, 6.3 V, X5R, 20%, 10 μ F, 0603	TDK	C1608X5R0J106K
C14	1	Capacitor, ceramic, 50 V, NPO, 10%, 15 pF, 0603	Std	Std
C15	1	Capacitor, ceramic, 50 V, X7R, 20%, 3.3 nF, 0603	Std	Std
C100	1	Capacitor, ceramic, 50 V, X7R, 20%, 4.7 nF, 0603	Std	Std
L1	1	Inductor, SMT, 27 A, 1.5 μ H, 2.5 m Ω , 0.508 x 0.520	Vishay	IHLP5050FDER1R5M01
Q1	1	MOSFET, N-channel, 30 V, 11A, 13.8 m Ω , SO-8	IR	IRF7807Z
Q2	1	MOSFET, N-channel, 30 V, 13.6 A, 9.1 m Ω , SO-8	IR	IRF7821
R1	1	Resistor, chip, 1/16 W, 5%, 10 k Ω , 0603	Std	Std
R2	1	Resistor, chip, 1/16 W, 5%, 1 Ω , 0603	Std	Std
R3	1	Resistor, chip, 1/16 W, 1%, 46.4 k Ω , 0603	Std	Std
R5	1	Resistor, chip, 1/16 W, 1%, 1.33 k Ω , 0603	Std	Std
R6	1	Resistor, chip, 1/16 W, 1%, 23.2 k Ω , 0603	Std	Std
R100	1	Resistor, chip, 1/4 W, 5%, 5.6 Ω , 1206	Std	Std
U1	1	IC, synchronous buck controller with 4-bit VID interface for Smart-Reflex DSPs, QFN-16	TI	TPS40197RGY

9.2.2 Detailed Design Procedure

For regulator stability, a 1- μ F capacitor is required to be connected from BP to GND. In some applications using higher gate charge MOSFETs, a larger capacitor is required for noise suppression. For a total gate charge of both the high-side and low-side MOSFETs greater than 20 nC, a 2.2- μ F or larger capacitor is recommended.

$$I_G = f_{SW} \times (Q_{G(\text{high})} + Q_{G(\text{low})})$$

where

- I_G is the required gate drive current
- f_{SW} is the switching frequency
- $Q_{G(\text{high})}$ is the gate charge requirement for the high-side FET when $V_{GS} = 5$ V
- $Q_{G(\text{low})}$ is the gate charge requirement for the low-side FET when $V_{GS} = 5$ V

(6)

10 デバイスおよびドキュメントのサポート

10.1 デバイス・サポート

10.1.1 デベロッパー・ネットワークの製品に関する免責事項

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10.2 ドキュメントのサポート

10.2.1 関連デバイス

以下の部品は特性が TPS40197 と類似で、検討対象となるものです。

TI 文書番号	デバイス	概要
SLUS719	TPS40192	パワー・グッド機能搭載、4.5V～18V 入力同期整流降圧型コントローラ
	TPS40193	

10.2.2 関連資料

TI 文書番号	ドキュメント タイプ	タイトル
SPRAAW7	アプリケーション・レポート	TMS320C6474 Hardware Design Guide (英語)
SLVA057	アプリケーション・レポート	Understanding Buck Power Stages in Switchmode Power Supplies (英語)
SLUP206	セミナー・シリーズ	Under the Hood of Low-Voltage DC/DC Converters (英語)、2003 年、SEM-1500
SLUP173	セミナー・シリーズ	Designing Stable Control Loops (英語)、2001 年、SEM-1400
SLMA002	アプリケーション・レポート	PowerPAD™ Thermally Enhanced Package (英語)
SLMA004	アプリケーション・レポート	PowerPAD™ Made Easy (英語)

10.3 ドキュメントの更新通知を受け取る方法

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Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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10.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

11 メカニカル、パッケージ、および注文情報

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS40197RGYR	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	40197
TPS40197RGYR.A	Active	Production	VQFN (RGY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	40197
TPS40197RGYT	Active	Production	VQFN (RGY) 16	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	40197
TPS40197RGYT.A	Active	Production	VQFN (RGY) 16	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	40197

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

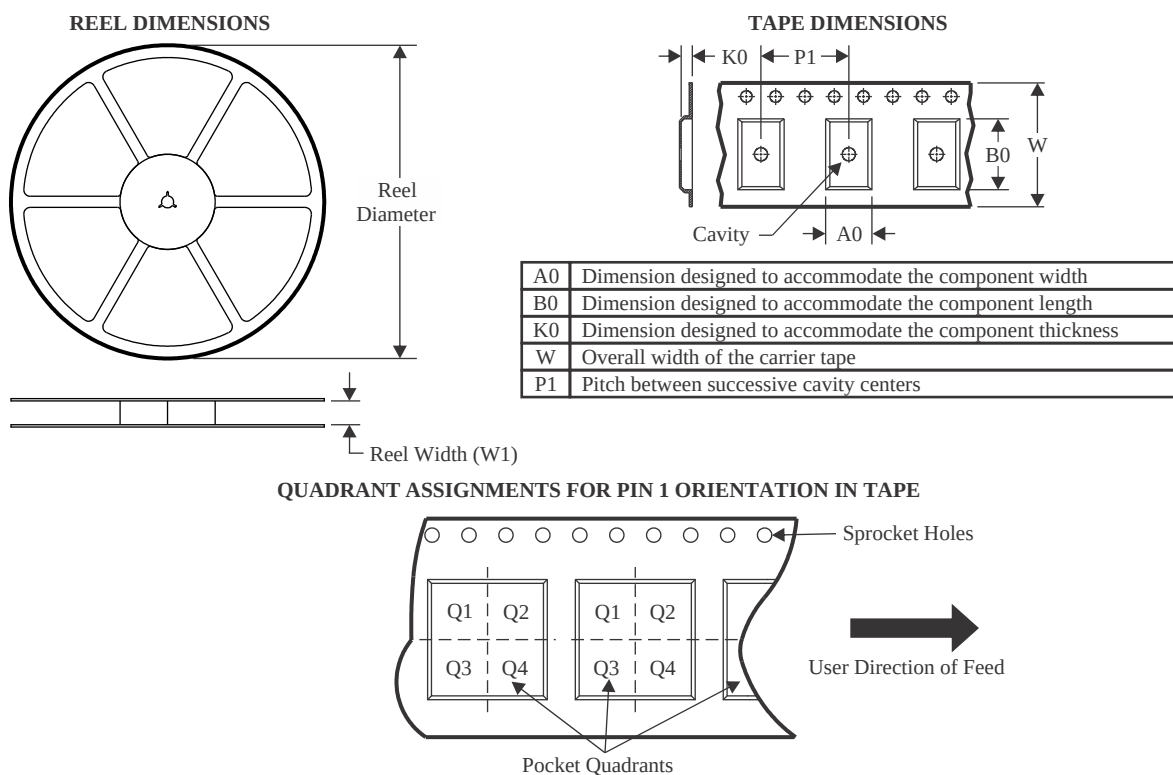
⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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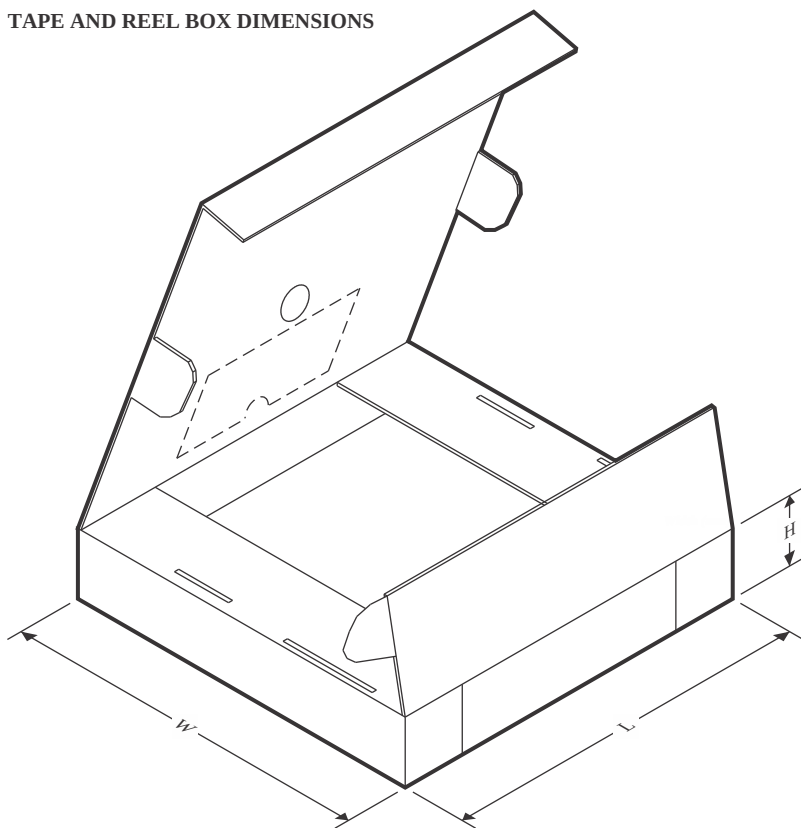
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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS40197RGYR	VQFN	RGY	16	3000	330.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1
TPS40197RGYR	VQFN	RGY	16	3000	330.0	12.4	3.71	4.21	1.11	8.0	12.0	Q1
TPS40197RGYT	VQFN	RGY	16	250	180.0	12.5	3.71	4.21	1.11	8.0	12.0	Q1
TPS40197RGYT	VQFN	RGY	16	250	180.0	12.4	3.8	4.3	1.5	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



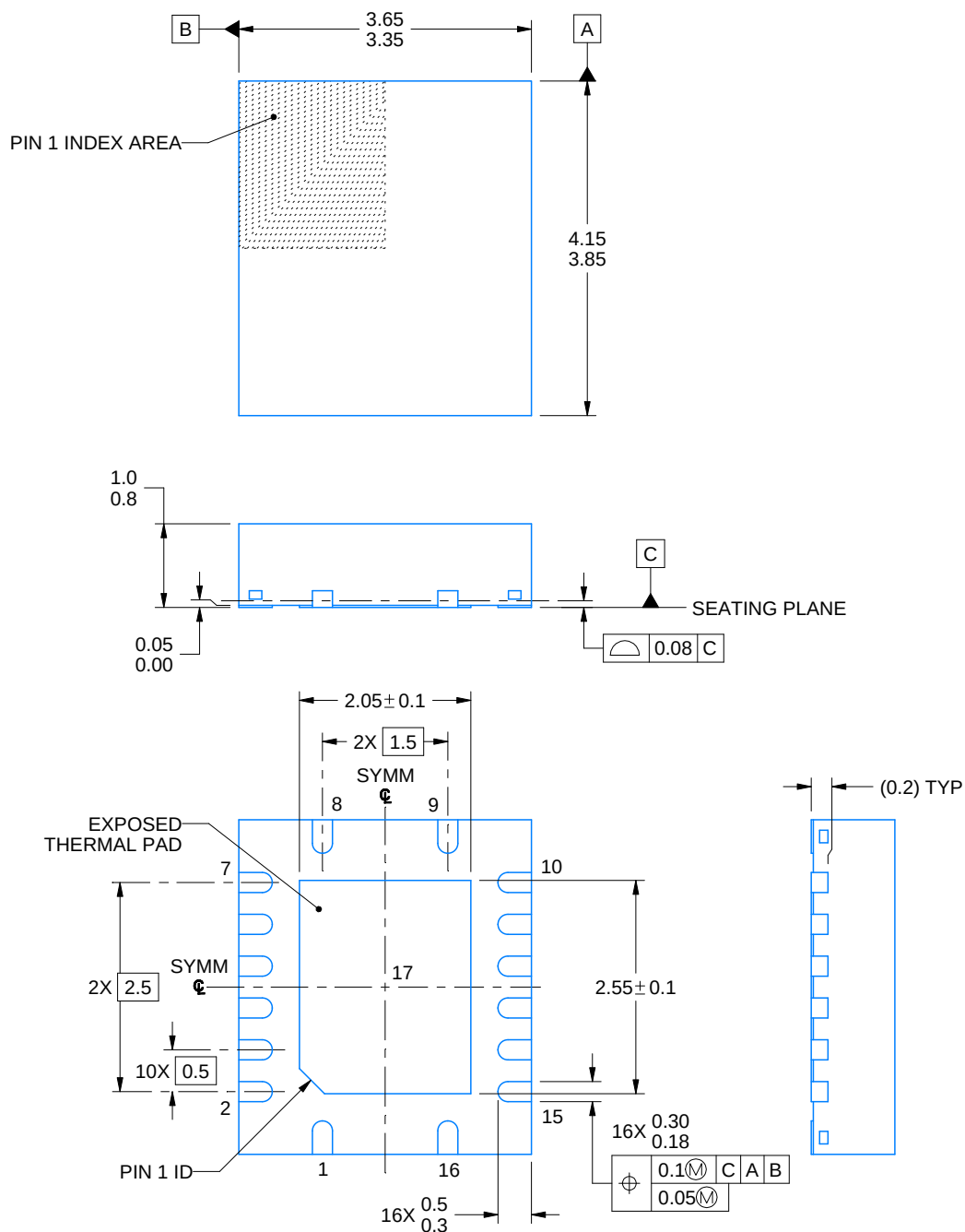
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS40197RGYR	VQFN	RGY	16	3000	353.0	353.0	32.0
TPS40197RGYR	VQFN	RGY	16	3000	338.0	355.0	35.0
TPS40197RGYT	VQFN	RGY	16	250	338.0	355.0	35.0
TPS40197RGYT	VQFN	RGY	16	250	213.0	191.0	35.0



VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4225140/A 07/2019

NOTES:

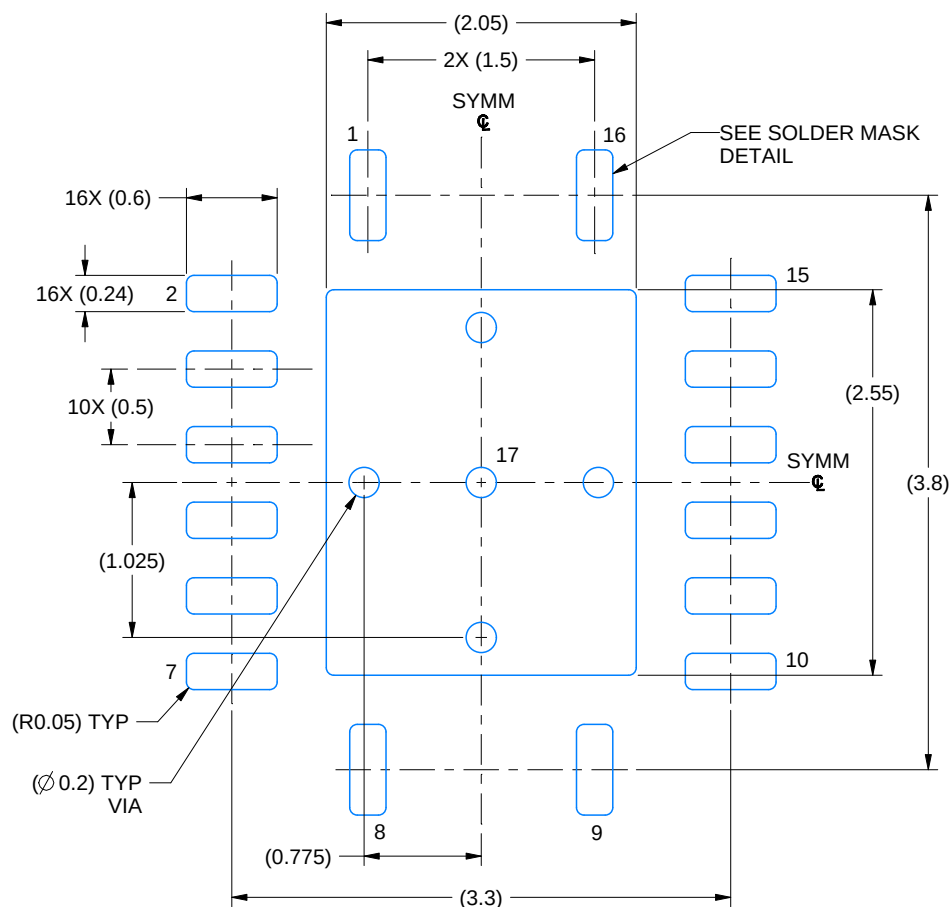
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

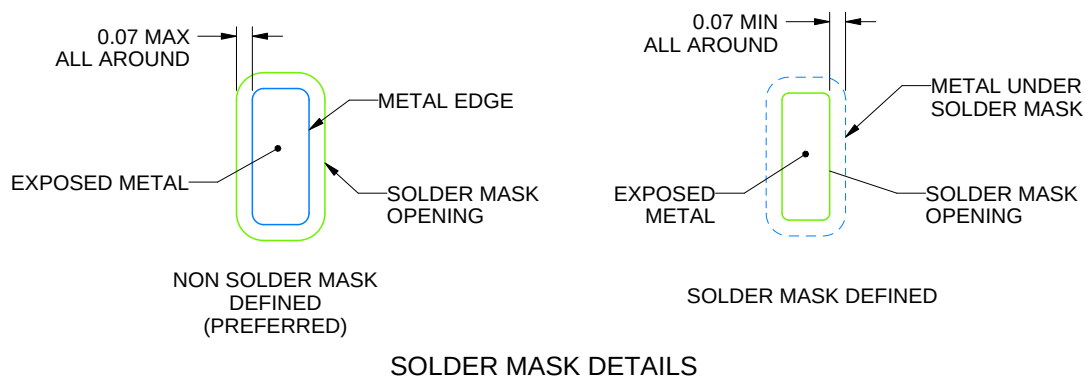
RGY0016A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



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NOTES: (continued)

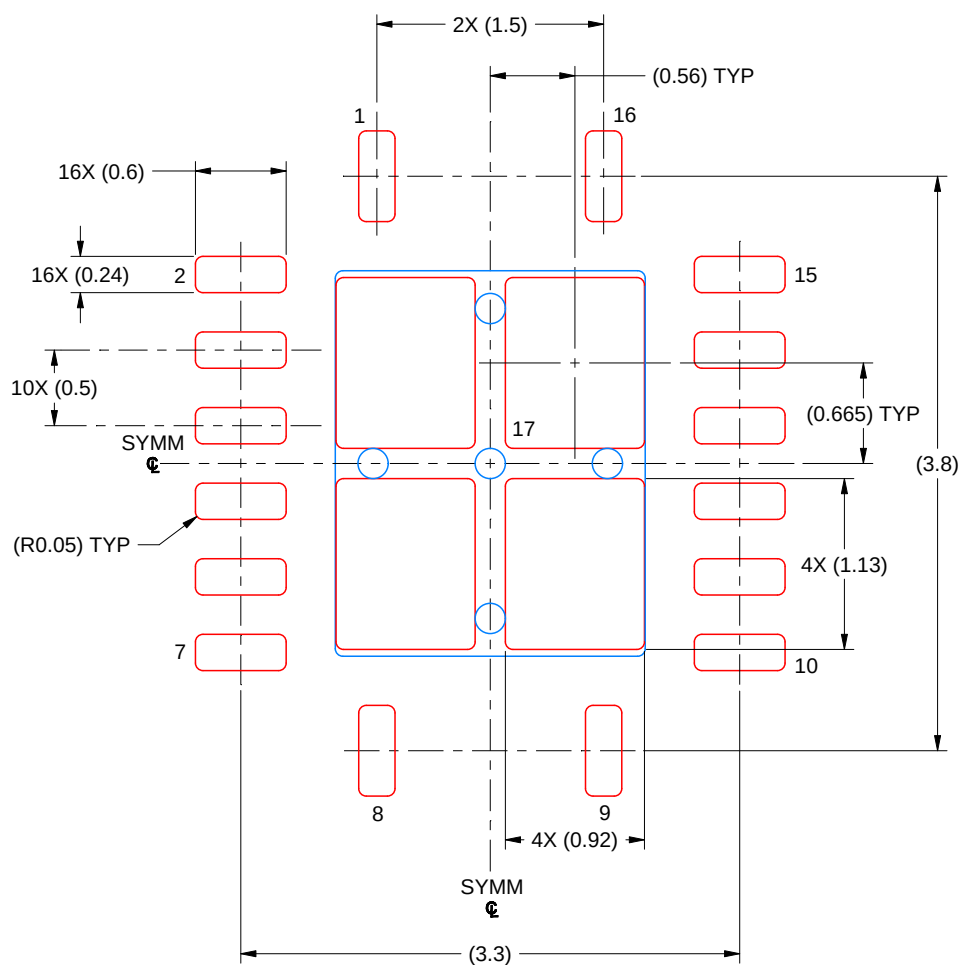
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGY0016A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK STENCIL
SCALE: 20X

EXPOSED PAD 17
80% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE

4225140/A 07/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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最終更新日：2025 年 10 月